

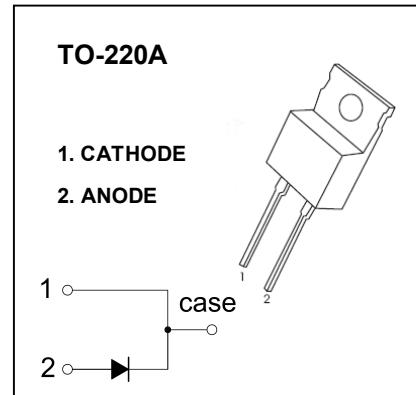
TO-220A Plastic-Encapsulate Diodes

SBL1030,35,40,45,50,60

SCHOTTKY BARRIER RECTIFIER

FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value						Unit
		SBL 1030	SBL 1035	SBL 1040	SBL 1045	SBL 1050	SBL 1060	
V_{RRM}	Peak repetitive reverse voltage							
V_{RWM}	Working peak reverse voltage	30	35	40	45	50	60	V
V_R	DC blocking voltage							
$V_{R(RMS)}$	RMS reverse voltage	21	24.5	28	31.5	35	42	V
I_o	Average rectified output current@ $T_c=95^\circ\text{C}$				10			A
I_{FSM}	Non-Repetitive peak forward surge current 8.3ms half sine wave				250			A
P_D	Power dissipation				2			W
R_{QJA}	Thermal resistance from junction to ambient				50			°C/W
T_j	Junction temperature				125			°C
T_{stg}	Storage temperature				-55~+150			°C

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Device	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(\text{BR})}$	SBL1030	$I_R=0.5\text{mA}$	30			V
		SBL1035		35			
		SBL1040		40			
		SBL1045		45			
		SBL1050		50			
		SBL1060		60			
Reverse current	I_R	SBL1030	$V_R=30\text{V}$				0.45 mA
		SBL1035	$V_R=35\text{V}$				
		SBL1040	$V_R=40\text{V}$				
		SBL1045	$V_R=45\text{V}$				
		SBL1050	$V_R=50\text{V}$				
		SBL1060	$V_R=60\text{V}$				
Forward voltage	V_F	SBL1030-1045	$I_F=10\text{A}$			0.55	V
		SBL1050,1060				0.7	